

Fast Recovery Epitaxial Diode (FRED)

preliminary data

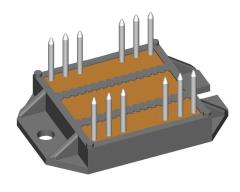
 $I_{FAVM} = 2x 147 A$

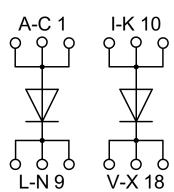
 $V_{RRM} = 600 V$

 $t_{xx} = 35 \text{ ns}$

Part number

DSEI2x161-06P





Features / Advantages:

- 2 independent FRED in 1 package
- · Planar passivated chips
- · Very short recovery time
- · Leads suitable for PC board soldering
- Very short recovery time
- · Soft recovery behaviour
- · Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- · Low noise switching
- · Small and light weight

Applications:

- Antiparallel diode for high frequency switching devices
- · Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating and melting
- Uninterruptible power supplies (UPS)
- · Ultrasonic cleaners and welders

Package: ECO-PAC2

- Isolation voltage: 3000 V~
- · Industry standard outline
- · RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

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IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified.

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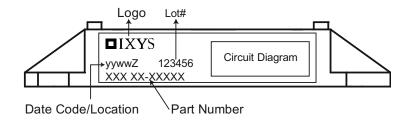
Diode				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
I _{FRMS}	RMS forward current		$T_{VJ} = T_{VJM}$			270	А
I _{FAVM} ①	max. average forward current	rectangular, d = 0.5	$T_{\rm C} = 70^{\circ} C$			147	Α
I _{FSM}	max. surge forward current	t = 10 ms (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	$T_{VJ} = 45^{\circ}C$			1200 1300	A A
		t = 10 ms (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	$T_{VJ} = 150^{\circ}C$			1080 1170	A A
l²t	Pt value for fusing	t = 10 ms (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	$T_{VJ} = 45^{\circ}C$			7200 7100	A ² s A ² s
		t = 10 ms (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	$T_{VJ} = 150^{\circ}C$			5800 5700	A²s A²s
I _R	reverse current	$V_{R} = V_{RRM}$ $V_{R} = 0.8 \cdot V_{RRM}$ $V_{R} = 0.8 \cdot V_{RRM}$	$T_{VJ} = 25^{\circ}C$ $T_{VJ} = 25^{\circ}C$ $T_{VJ} = 125^{\circ}C$			12 3 80	mA mA mA
V _F	forward voltage	I _F = 200 A	$T_{VJ} = 25^{\circ}C$			1.45	V
V _{TO}	threshold voltage slope resistance	for power-loss calculations only $T_{VJ} = T_{VJM}$				0.85 2.7	V mΩ
R _{thJC}	thermal resistance junction to case thermal resistance junction to heatsink				0.20	0.29	K/W K/W
I _{RM}	max. reverse recovery current	$I_F = 100 \text{ A}; -di_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 100 \text{ V}; \text{ L} \le 0.05 \mu\text{H}$	T _{VJ} = 100°C		45		А
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; -di/dt = 400 \text{ A/}\mu\text{s}; V_R = 30 \text{ V}$	$T_{VJ} = 25^{\circ}C$		35		ns

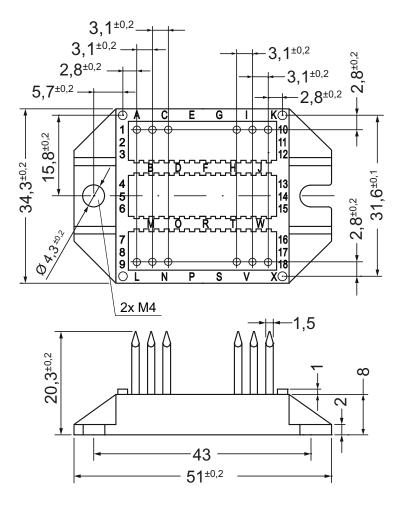
① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , V_{R} = 0.8 V_{RRM} , duty cycle d = 0.5



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Package	ECO-PAC2			Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
I _{RMS}	RMS current per terminal				100	Α	
T _{VJ} T _{op} T _{stg}	virtual junction temperature operation temperature storage temperature		-40 -40 -40		150 125 125	°C °C °C	
Weight					24		g
M _D	mounting torque			1.4		2.0	Nm
d _{Spp/App} d _{Spb/Apb}	creepage distance on surface striking distance through air		terminal to terminal terminal to backside	6.0 10.0			mm mm
V _{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RM	S; I _{ISOL} ≤ 1 mA	3000 2500			V





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